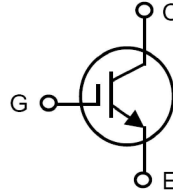


**1200V XPT™
GenX4™ IGBT**

**IXYA20N120B4HV
IXYP20N120B4**

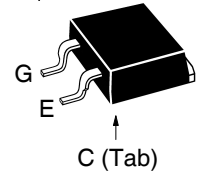
V_{CES} = 1200V
I_{C110} = 20A
V_{CE(sat)} ≤ 2.1V
t_{fi(typ)} = 90ns

Extreme Light Punch Through
IGBT for up to 5 - 30kHz Switching

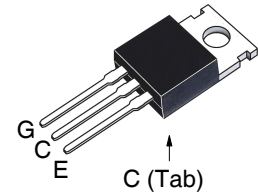


Symbol	Test Conditions	Maximum Ratings	
V _{CES}	T _J = 25°C to 175°C	1200	V
V _{CGR}	T _J = 25°C to 175°C, R _{GE} = 1MΩ	1200	V
V _{GES}	Continuous	±20	V
V _{GEM}	Transient	±30	V
I _{C25}	T _C = 25°C	76	A
I _{C110}	T _C = 110°C	20	A
I _{CM}	T _C = 25°C, 1ms	130	A
SSOA (RBSOA)	V _{GE} = 15V, T _{VJ} = 150°C, R _G = 10Ω Clamped Inductive Load	I _{CM} = 40 V _{CE} ≤ 0.8 • V _{CES}	A
P _C	T _C = 25°C	375	W
T _J		-55 ... +175	°C
T _{JM}		175	°C
T _{stg}		-55 ... +175	°C
T _L	Maximum Lead Temperature for Soldering	300	°C
T _{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
M _d	Mounting Torque (TO-220)	1.13/10	Nm/lb.in
F _C	Mounting Force (TO-263HV)	10..65 / 22..14.6	N/lb
Weight	TO-263HV	2.5	g
	TO-220	3.0	g

**TO-263HV
(IXYA..HV)**



**TO-220
(IXYP)**



G = Gate D = Collector
E = Emitter Tab = Collector

Features

- Optimized for 5-30kHz Switching
- Positive Thermal Coefficient of V_{ce(sat)}
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions (T _J = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	I _C = 250μA, V _{GE} = 0V	1200		V
V_{GE(th)}	I _C = 250μA, V _{CE} = V _{GE}	4.0		6.5 V
I_{CES}	V _{CE} = V _{CES} , V _{GE} = 0V T _J = 150°C			25 μA 5 mA
I_{GES}	V _{CE} = 0V, V _{GE} = ±20V			±100 nA
V_{CE(sat)}	I _C = 20A, V _{GE} = 15V, Note 1 T _J = 150°C	1.83 2.18		2.10 V V

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 20\text{A}, V_{CE} = 10\text{V}$, Note 1	7.5	12.5	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		890	pF
C_{oes}			58	pF
C_{res}			33	pF
$Q_{g(on)}$	$I_C = 20\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		44	nC
Q_{ge}			8	nC
Q_{gc}			20	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 20\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.8 \cdot V_{CES}, R_G = 10\Omega$ Note 2		15	ns
t_{ri}			47	ns
E_{on}			3.9	mJ
$t_{d(off)}$			200	ns
t_{fi}			90	ns
E_{off}			1.6	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 20\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.8 \cdot V_{CES}, R_G = 10\Omega$ Note 2		13	ns
t_{ri}			35	ns
E_{on}			4.6	mJ
$t_{d(off)}$			270	ns
t_{fi}			170	ns
E_{off}			2.7	mJ
R_{thJC}	TO-220			0.40 $^\circ\text{C}/\text{W}$
R_{thCS}		0.50		$^\circ\text{C}/\text{W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher V_{CE} (clamp), T_J or R_G .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2
by one or more of the following U.S. patents: 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

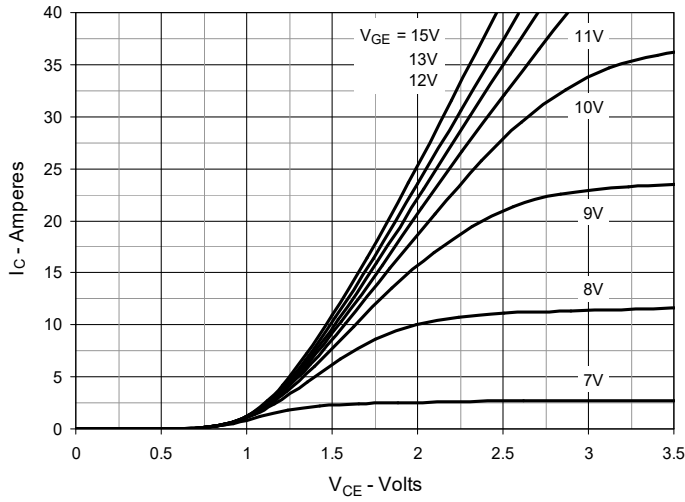


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

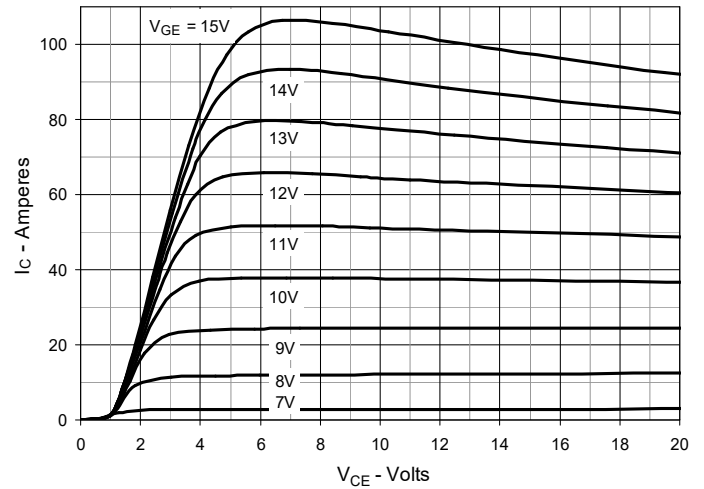


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

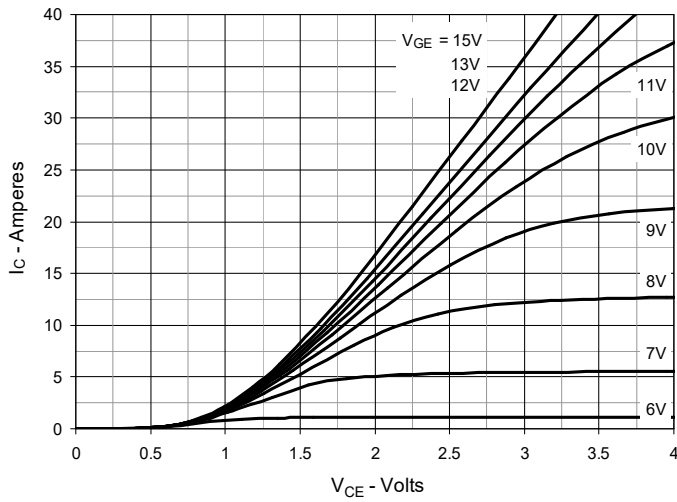


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

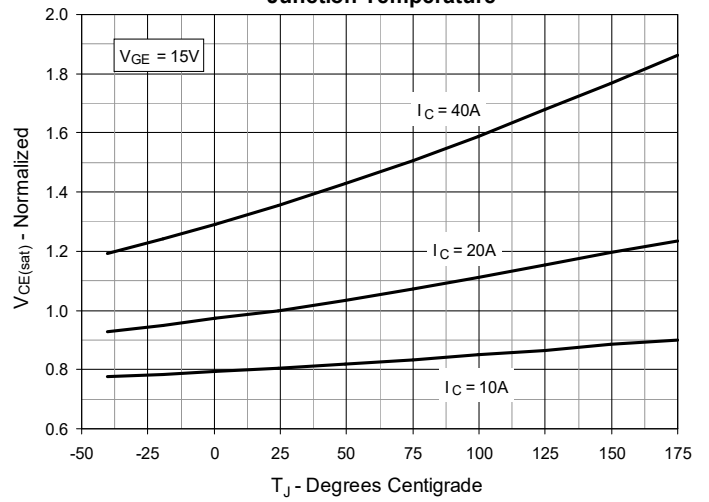


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

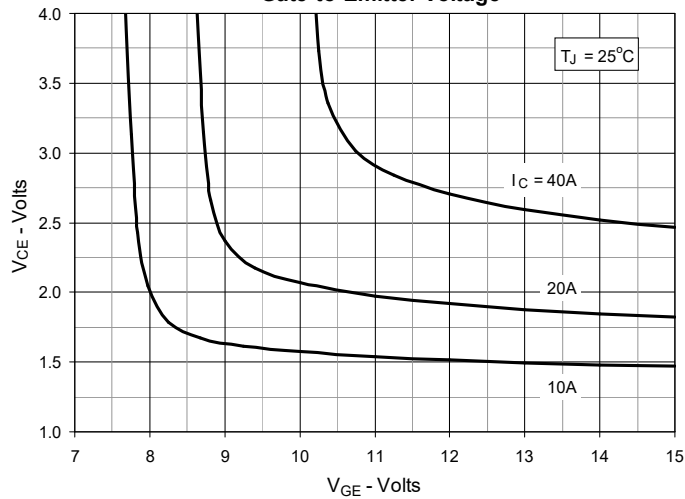


Fig. 6. Input Admittance

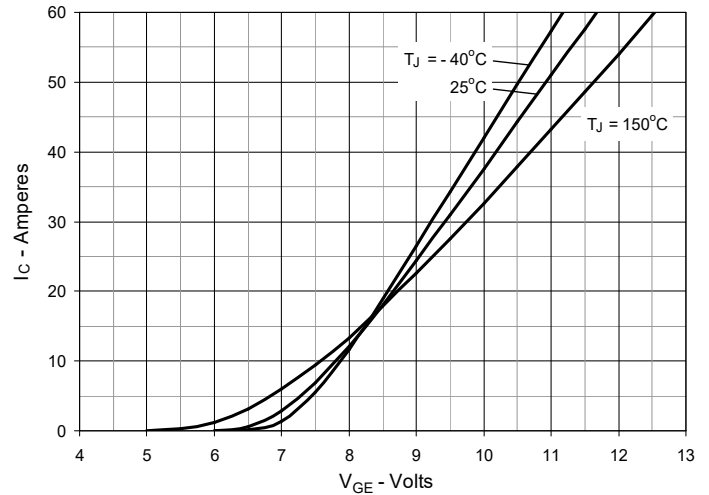


Fig. 7. Transconductance

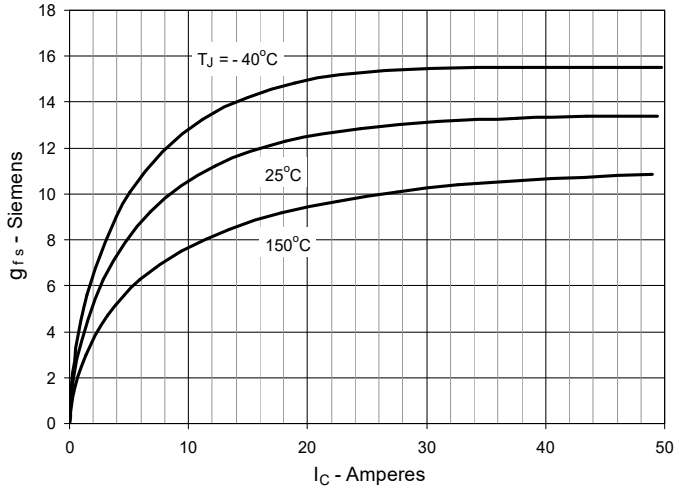


Fig. 8. Gate Charge

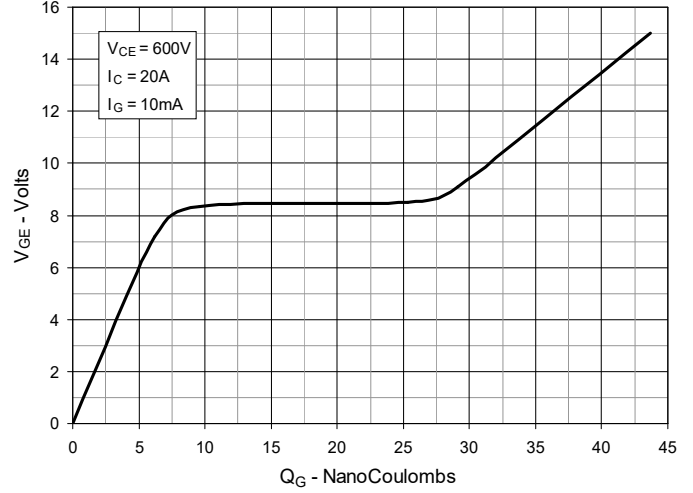


Fig. 9. Capacitance

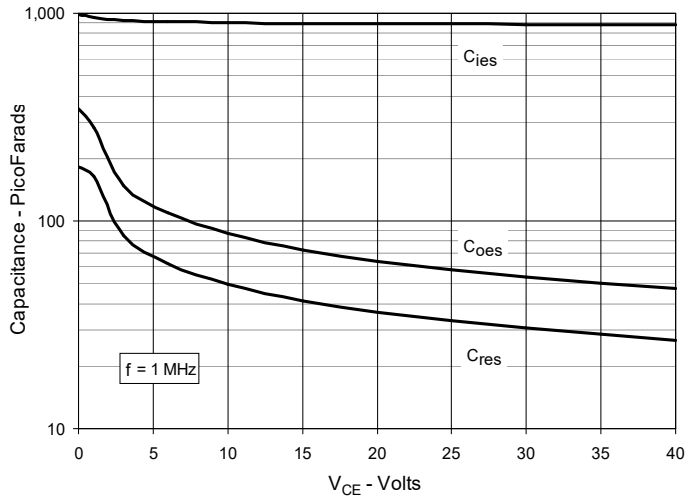


Fig. 10. Reverse-Bias Safe Operating Area

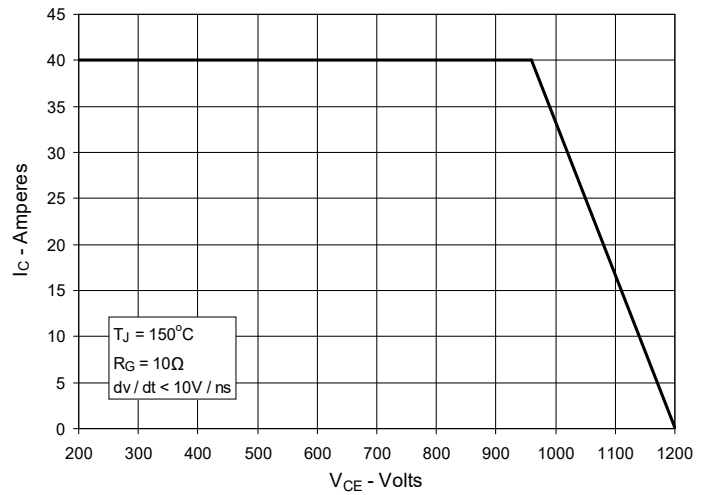


Fig. 11. Maximum Transient Thermal Impedance

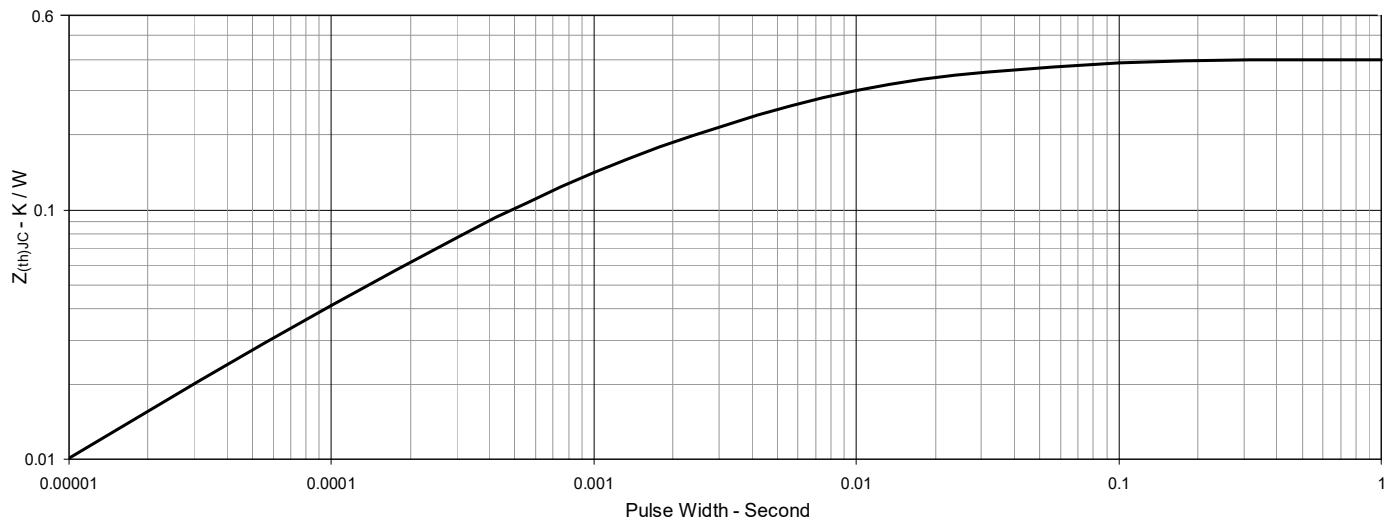


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

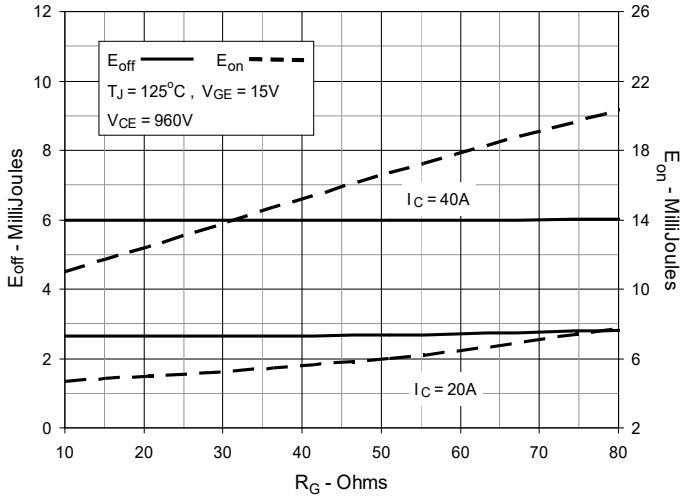


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

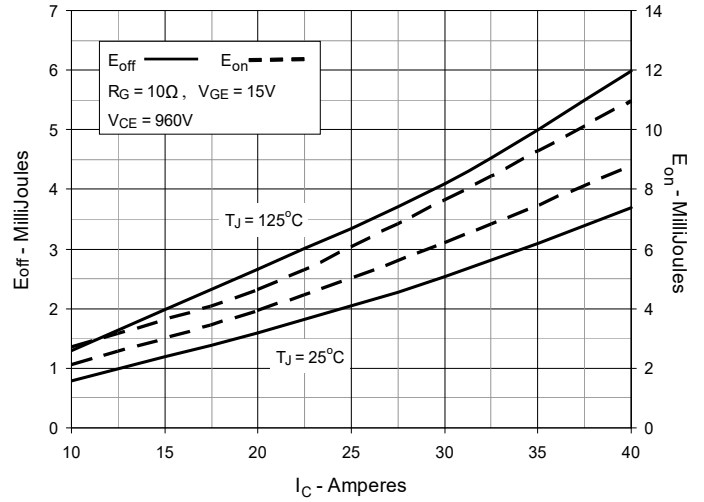


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

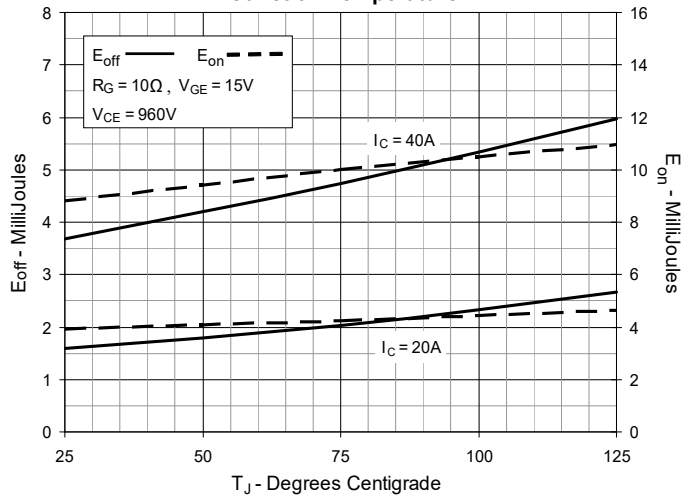


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

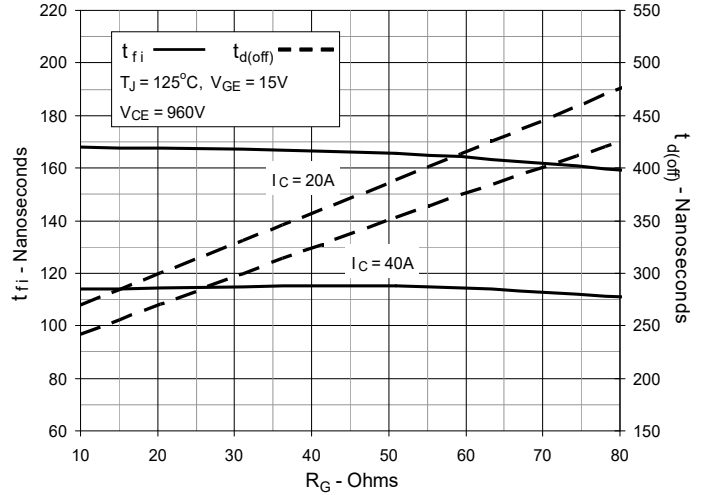


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

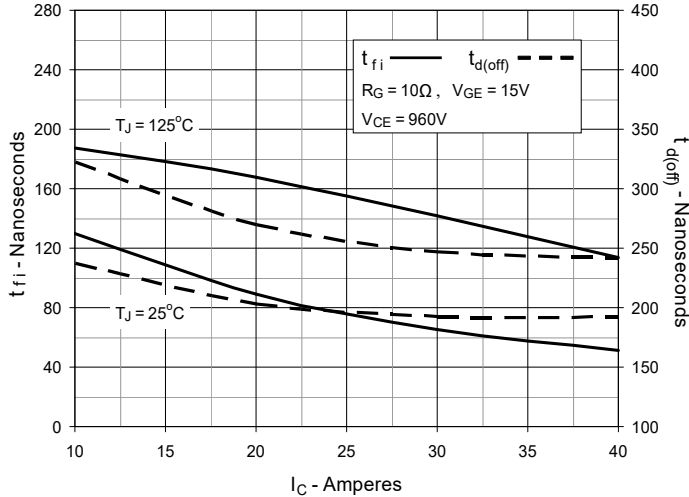


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

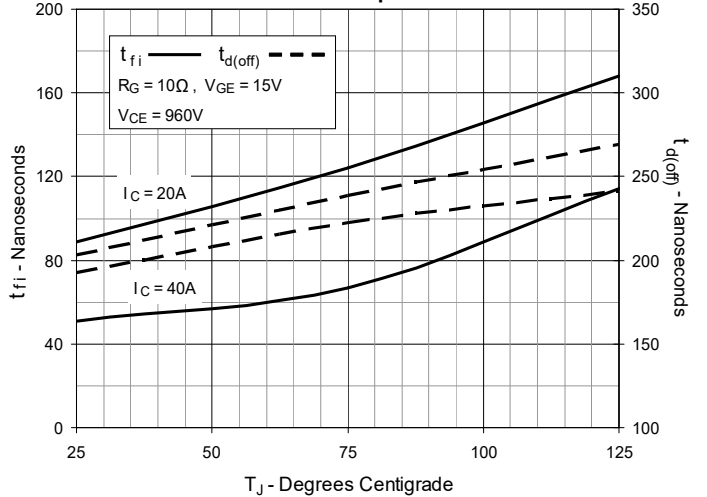


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

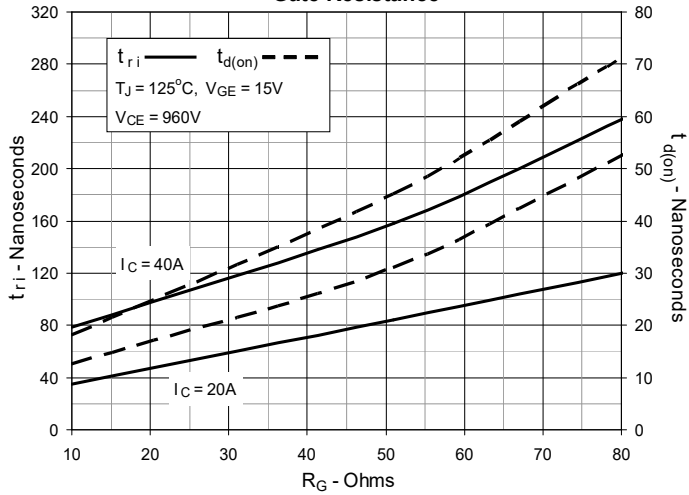


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

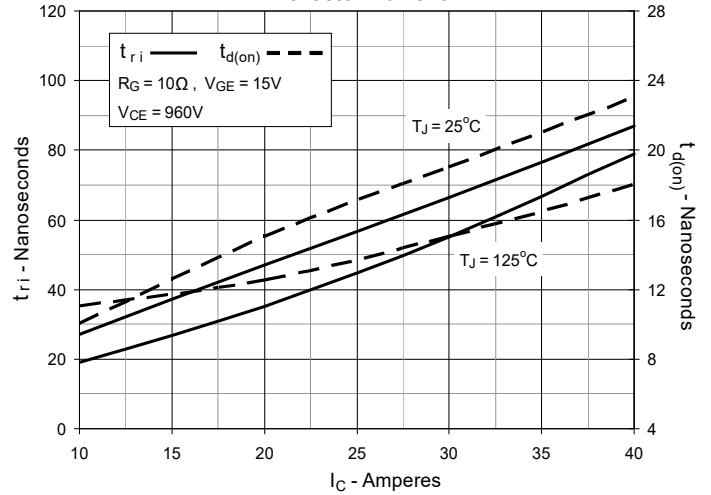
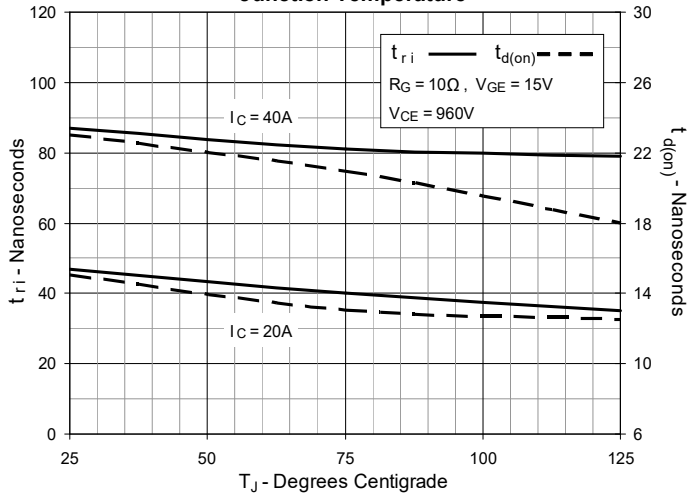
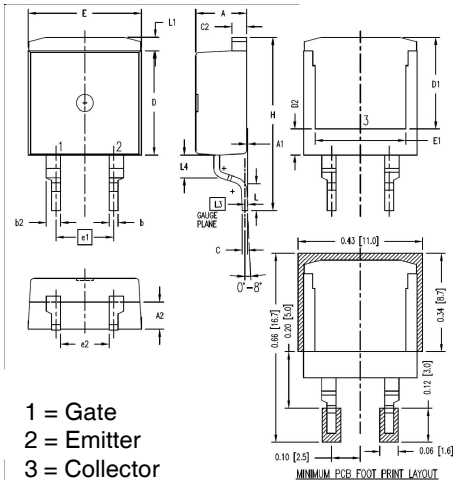
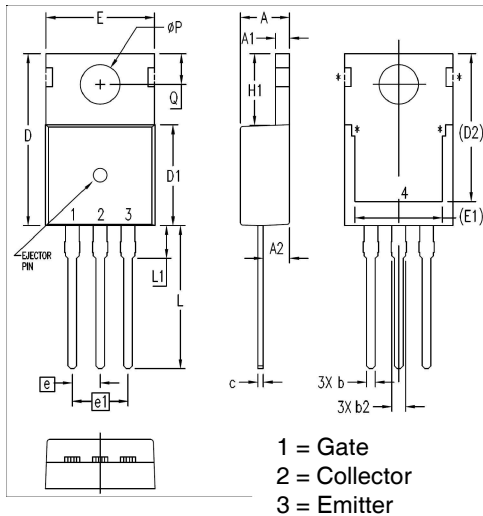


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature



TO-263HV Outline


SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.054	1.18	1.38
C	.018	.024	0.45	0.60
C2	.049	.055	1.25	1.40
D	.354	.370	9.00	9.40
D1	.311	.327	7.90	8.30
D2	.083	.098	2.10	2.50
E	.386	.402	9.80	10.20
E1	.307	.323	7.80	8.20
e1	.200 BSC		5.08 BSC	
(e2)	.163	.174	4.13	4.43
H	.591	.614	15.00	15.60
L	.079	.102	2.00	2.60
L1	.039	.055	1.00	1.40
L3	.010 BSC		0.254 BSC	
(L4)	.071	.087	1.80	2.20

TO-220 Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.047	.055	1.20	1.40
A2	.079	.106	2.00	2.70
b	.024	.039	0.60	1.00
b2	.045	.057	1.15	1.45
c	.014	.026	0.35	0.65
D	.587	.626	14.90	15.90
D1	.335	.370	8.50	9.40
(D2)	.500	.531	12.70	13.50
E	.382	.406	9.70	10.30
(E1)	.283	.323	7.20	8.20
e	.100 BSC		2.54 BSC	
e1	.200 BSC		5.08 BSC	
H1	.244	.268	6.20	6.80
L	.492	.547	12.50	13.90
L1	.110	.154	2.80	3.90
ØP	.134	.150	3.40	3.80
Q	.106	.126	2.70	3.20

